NSN 5961-01-050-7917

Thyristor Semiconductor Device - Page 1 of 1

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Inclosure Material:

Glass and metal

Overall Length:

0.190 inches

Overall Diameter:

Between 0.592 inches and 0.660 inches

Internal Configuration:

Junction contact

Electrode Internally-electrically Connected To Case:

Gate

Mounting Method:

Press fit

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

100.0 repetitive peak reverse voltage

Current Rating Per Characteristic:

12.00 amperes forward current, total rms watts

Power Rating Per Characteristic:

5.0 watts small-signal input power, common-collector blank

Maximum Operating Tempurature Per Measurement Point:

110.0 degrees celsius ambient air

Special Features:

Junction pattern arrangement: pnpn

Test Data Document:

82577-925947 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

3 ribbon

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

A110a0